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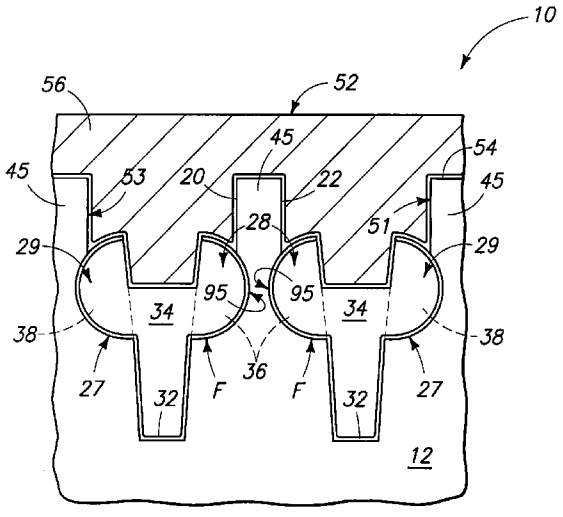
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(54) **Title:** METHODS OF FORMING FIELD EFFECT TRANSISTORS, PLURALITIES OF FIELD EFFECT TRANSISTORS, AND DRAM CIRCUITRY COMPRISING A PLURALITY OF INDIVIDUAL MEMORY CELLS



(57) **Abstract:** A method of forming a field effect transistor includes forming trench isolation material within a semiconductor substrate and on opposing sides of a semiconductor material channel region along a length of the channel region. The trench isolation material is formed to comprise opposing insulative projections extending toward one another partially under the channel region along the channel length and with semiconductor material being received over the projections. The trench isolation material is etched to expose opposing sides of the semiconductor material along the channel length. The exposed opposing sides of the semiconductor material are etched along the channel length to form a channel fin projecting upwardly relative to the projections. A gate is formed over a top and opposing sides of the fin along the channel length. Other methods and structures are disclosed.

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